## **Electronic Supplementary Information**

## Fabrication of Multi-layered DNA Nanostructures Using Single-strand and Double-crossover Tile Connectors<sup>†</sup>

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## **15 Materials and Methods**

**DNA lattice fabrication.** Synthetic oligonucleotides purified via High-Performance Liquid Chromatography (HPLC) were purchased from Bioneer (Daejeon, Korea). The DNA nanostructures were formed by mixing a stoichiometric quantity of each strand in physiological 1× TAE/Mg<sup>2+</sup> buffer 20 [40 mM Tris, 20 mM Acetic acid, 1 mM EDTA (pH 8.0), and 12.5 mM magnesium acetate]. We

- 20 [40 mM Tris, 20 mM Acetic acid, 1 mM EDTA (pH 8.0), and 12.5 mM magnesium acetate]. We adopted a SAG method with mica as a substrate to form the base layer. This method involved three steps: seeding, nucleation and finally lattice structure formation. The electrostatic interaction between the DNA tiles and the mica sheets created a constructive environment for lattice formation, and as depicted in Figure 1-(c), a number of unit tiles laid the foundation of the structure by randomly seeding
- 25 on the mica substrate. Subsequently, the complementary sticky ends hierarchically assembled from the seeding tiles, resulting in lattice growth. A multi-step annealing method was employed to construct the double-layer and multi-layered structure. However, we used a free-solution annealing method to form individual tiles.
- 30 Free-solution annealing to form SAC, DAC, DGT, EL tiles (Tiles of single strand-based design) and DXA<sub>1</sub>, DXB<sub>1</sub> (Tiles of DX-based design). 200 nM each of SAC, DAC, DGT, EL tiles and DXA<sub>1</sub>, DXB<sub>1</sub> tiles were formed by mixing a stoichiometric quantity of each of their strands in 1× TAE/Mg<sup>2+</sup> buffer. These tile strand mixtures were annealed in a test tube by slowly cooling from 95 down to 25 °C in a Styrofoam box.
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**Mica-assisted growth (MAG) to form the base layer.** A 50 nM base layer was formed by mixing a stoichiometric quantity of each strand of two pair of tiles, SGT, EB and DXA<sub>1</sub>, DXB<sub>0</sub> in case of single strand-based and DX tile-based design, respectively, with cleaved mica substrate ( $5 \times 5 \text{ mm}^2$ ) in  $1 \times \text{TAE/Mg}_{2^+}^{2+}$  in a test tube, as shown in Figure 1-(c). To facilitate selective hybridization, the mixture of

40 the two tile strands with the mica substrate was annealed in a test tube by slowly cooling them from 95 down to 25°C for 24 hours in a Styrofoam box containing 2 L of boiled water. This resulted in the formation of base layer.

**Multi-step annealing to form double-layer and multi-layered structures.** The mica substrate of the 45 pre-formed base layer was inserted in a new test tube containing 50 nM of pre-annealed layering and connector tiles at a volume of 200  $\mu$ L. These samples were then cooled from 42 to 25 °C in a Styrofoam box for 24 hours to facilitate DNA hybridization for double- and multi-layer formation [Figure 1-(d)]. At the end of each annealing step, the sample was incubated overnight at 4°C to ensure structural stability.

**AFM imaging.** AFM imaging of the samples prepared via MAG involved taking the mica substrate from a test tube and placing it on a metal puck with instant glue. Then, 30  $\mu$ L of 1× TAE/Mg<sup>2+</sup> buffer were pipetted onto the substrate, and another 20  $\mu$ L of 1× TAE/Mg<sup>2+</sup> were dispensed onto a silicon nitride AFM tip (Veeco Inc. USA). Imaging was carried out for the samples prepared via free-solution

55 annealing by dropping 5  $\mu$ L of DNA sample on freshly cleaved mica surface. 30  $\mu$ L of 1× TAE/Mg<sup>2+</sup>

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were then placed onto the mica, and another 20  $\mu$ L of 1× TAE/Mg<sup>2+</sup> were placed onto the silicon nitride AFM tip. AFM images were then obtained by using a Multimode Nanoscope (Veeco Inc., USA) in the fluid tapping mode.

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**Table S1.** Schematics of different tiles with their respective strands involved in the assembly of DX multi-layer nanostructure using single-strand DNA as a connector. The name of each strand and the 10 sticky-end sequences are indicated as well.

Layer	Tile	Scheme
Base- layer	ICCAA GCGT CCAC TTGG GCAG TAGG ACGC CTCG S4   TIGCTA CGTT CGCA GGTG AACC CGTC ATCC TGCG GAGC CATAC   SGT1 SGT SGT2 SGT4   ACTAC CGAA AGCC TGAG CTAG SGT2 SGT4   SGT SGT2 SGT4 SGT4   SGT5 SGT3 SGT3 SGT3   TGTGTGTGTGTGTGTGTGTGTGTGTGTGTGTGTGTGTG	EB2 GATG ATGT CCTT GTAA TGAA GCGG ACAA CGAG S3" CACTT CTAC TACA GGAA CATT ACTT CGCC TGTT GCTC TGATG EB1 GTATG GAAC GACC GACC TGAT TGCG TGAT TGCG S4" CTTG CTGG ACTA ACGC ATTA GAGT CCGT AAGC
Double- layer	HP Up SZ CAG CAG CAG CAG TAGG ACGC CTCG CTAGT CGTC GCA GGTG AACC CTAGT CGTA GGC ACGC CTCG DAC1 TCACT CGAA AGCC TGAG CTAG DAC2 TCACT CGAA AGCC TGAG CTAG DAC2 CCTT TCGG ACTC GATC DAC3 CCTT TCGG ACTC GATC DAC3 CCTT TCGG ACTC GATC CACT CGAA GGT CTGT CCAG TAGC CGTC TGG CAGAC CGTC TGG ACTC GATC CACT CGAA CCC CGTC CACT CGAA CCC CGTC CACT CGAA CCC CGTC CGTC TCGG ACTC GATC CGTC TGG CGAC CGTC TGG CGTC TGG CGAC CGTC TGG CGTC T	EL2 GATG ATGT CCTT GTAA TGAA GCGG ACAA CGAG S3' GTTCT CTAC TACA GGAA CATT ACTT CGCC TGTT GCTC AGTGA EL1 GAGAT GAAC GAAC S4' CTTG CTGG ACTA ACGC ATTA GAGT CCGT AAGC
Multi- layer	HP Down Sev Sev Sev DGT6 GCAA GCGT CCAC TIGG CTAGT GGT GCAC CGTC TIGG GGTG AACC CGTC TIGG GGTG AACC CGTC TIGG GGTG CTGC CGTC ATCG CAAGA CGTC TIGG GGTC TIGG GGTC ATCG CAAGA CGTC TIGG GGTC TIGG GGTC TIGG CAAGA CGTC TIGG GGTC TIGG GGTC TIGG CAAGA CGTC TIGG GGTC TIGG GGTC TIGG CAAGA CGTC TIGG GGTC TIGG CAAGA CGTC TIGG GGTC TIGG CAAGA CGTC TIGG GGTC TIGG GGTC TIGG CAAGA CGTC TIGGG GGTC TIGG GGTC TIGG CAAGA CGTC TIGG GGTC TIGG GGTC TIGG GGTC TIGG TIGG	EL2 GATG ATGT CCTT GTAA 53' GTTCT CTAC TACA GGAA CATT CGAA GCGG ACAA CGAG 52' GTTCT CTAC TACA GGAA CATT ACTT CGCC TGTT GCTC AGTGA EL1 GAGAT GAAC GAAC GACC TGAT TGCG TAAT CTCA GGCA TTCG GATCA 54' CTTG CTGG ACTA ACGC ATTA GAGT CCGT AAGC

Strand	Base	Sequence (5' to 3')
SGT		
SGT1	26	TGCTACGTTCGCACCGAAAGCCATCA
SGT2	32	TCCAGACACCTACTGCGGTTCACCTGCGAACG
SGT3	48	CGATGACCTGTCTGGAGATCGAGTGGTGAACCGCAGTAGGACGCCTCG
SGT4	26	CATCACGAGGCGTGGTCATCGGTGAA
SGT5	48	GCTTTCGGACTCGATCTTGTGTGTGTGTGTGTGTGTGTGT
EB		
EB1	26	GTATGGAACGACCACATCATCTTCAC
EB2	48	GATGATGTCCTTGTAAACTTCGCCACTCTAATCGCAATCAGGTCGTTC
EB3	48	GAGCAACAGGCGAAGTTTACAAGGTGATTGCGATTAGAGTCCGTAAGC
EB4	26	TAGCAGCTTACGG TGTTGCTCTGATG
EL		
EL1	26	GAGATGAACGACCACATCATCTCTTG
EL2	48	GATGATGTCCTTGTAAACTTCGCCACTCTAATCGCAATCAGGTCGTTC
EL3	48	GAGCAACAGGCGAAGTTTACAAGGTGATTGCGATTAGAGTCCGTAAGC
EL4	26	ACTAGGCTTACGGTGTTGCTCAGTGA
DAC		
DAC1	26	CTAGTCGTTCGCACCGAAAGCTCACT
DAC2	16	GATCGAGTGGTGAACC
DAC3	48	GCTTTCGGACTCGATCTCCAGACACCTACTGCGGTTCACCTGCGAACG
DAC4	26	ATCTCCGAGGCGTGGTCATCGCAAGA
DAC5	48	CGATGACCTGTCTGGATTACACACACACACACACACACAC
DAC6	48	ACACACACACACACACACACACACACACACACTTGCAGTAGGACGCCTCG
DGT		
DGT1	26	CTAGTCGTTCGCACCGAAAGCTCACT
DGT2	16	GATCGAGTGGTGAACC
DGT3	48	GCTT TCGGACTCGATCTCCAGACACCTACTGCGGTTCACCTGCGAACG
DGT4	26	ATCTCCGAGGCGTGGTCATCGCAAGA
DGT5	48	CGATGACCTGTCTGGATTGTGTGTGTGTGTGTGTGTGTGT
DGT6	48	GT

**Table S2.** Details of the names of the strands, number of bases in each strand, and base sequence composition from the 5' to 3' direction required for multi-layer assembly.

**Table S3.** Schematic representation of two tiles (A-tile and B-tile) and their respective strands required to construct 3D-T based nanostructures in which a DX tile is used as a connector. (a)  $DXA_1$  tile, (b)  $DXB_0$  tile (connector tile), and (c)  $DXB_1$  tile. Insets in (a) and (c) show the 3D view of A-tile and B-tile, respectively. The sticky ends and their sequences are represented in green and in red, respectively.



Strand	Base	Sequence (5' to 3')
DXA1		
DXA1-1	32	CATTCTGGACGCCATAAGATAGCACCTCGACT
DXA1-2	26	CATACCTACCGCACCAGAATGTGCTA
DXA1-3	26	TCACTCGATCCGTGGCTACTGCTAGT
DXA1-4	16	CAGTAGCCTGCTATCT
DXA1-5	30	GCCAGTGGTAGGAGCATTTGCCTGCGGTAG
DXA1-6	78	CCTACCTGCGAATCTCTGTAGTGGTGTCGTCTGCTCGGACTGG CTGTATGGCGTGGCAAATGAGTCGAGGACGGATCG
DXA1-7	48	CAATGCGGACTACAGAGATTCGCACCGAGCAGACGACACCTG AGACGG
DXA1-8	26	TTCACCCGTCTCACCGCATTGTGATG
DXB0		
DXB0-1 (=DXB1-1)	26	AGTGAGGCAATCCACAACCGCACTAG
DXB0-2	48	GCGGTTGTCCAACTTACCAGATCCACAAGCCACGTTACAGGAT TGCC
DXB0-3 (=DXB1-3)	26	GTATGGCGAACGGTGTAGAGCTAGCA
DXB0-4	48	GCTCTACAGGATCTGGTAAGTTGGTGTAACGCGGCTTGTCCGT TCGC
DXB1		
DXB1-2	32	GCGGTTGTCCAACTTACCAGATCCACAAGCCG
DXB1-4	16	GCTCTACAGGATCTGG
DXB1-5	30	ATTGGTGGTACTCGACGTTACAGGATTGCC
DXB1-6	78	AGTACCTGGATGTTCATAGCGTGGTGTCTCTCTTAGGACCA ATGCTAAGTTGGTGTAACGTGGCTTGTCCGTTCGC
DXB1-7	48	GTTTGAGGACGCTATGAACATCCACCTAAGCGAGACACC TGCCGAGC
DXB1-8	26	GTGAAGCTCGGCACCTCAAACCATCA

**Table S4.** Details of the names of the strands, number of bases, and sequence composition from 5' to 3' direction required for multi-layer assembly.

Figure S1. A 2% agarose gel image (ethidium bromide stained) showing association complexes of equimolar combination (200 nM) of various DNA cross-tiles in order to check the purities of DNA tiles involved in the assembly of multi-layered DNA nanostructures. DNA tiles were loaded in the gel as; EB (148 nt), EL (148), SGT (180), SAC (180), DAC (212), DGT (212), DXB0 (148), DXA1 (284), 5 and DXB1 (284) in the lanes 2, 3, 4, 5, 6, 7, 8, 9, and 10, respectively. 25 bp DNA Ladders were shown in lanes 1 and 11.



**Figure S2.** AFM image and height profile of the multi-layer assembly comprised of layering  $DXA_1$  and  $DXB_1$  tiles obtained via scratch method (contact mode AFM operation). Scale bar in an image is 1  $\mu$ m.



